

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	140	(semiconductor or wafer or substrate) and (active near4 region) and "nFET" and "pFET" and (gate near4 electrode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/15 16:59
S2	1	(semiconductor or wafer or substrate) and (active near4 region) and "nFET" and "pFET" and (gate near4 electrode) and (bond\$4 near4 (semiconductor or wafer or substrate)) and (open\$4 or via or trench or hole) and (implant\$4 near4 oxygen) and (anneal or heat or thermal) and stress and (current near8 flow)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 11:05
S3	4	(semiconductor or wafer or substrate) and (active near4 region) and "nFET" and "pFET" and (gate near4 electrode) and (bond\$4 near4 (semiconductor or wafer or substrate)) and (open\$4 or via or trench or hole) and stress and (current near8 flow)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 11:56
S4	13	(semiconductor or wafer or substrate) and (active near4 region) and "nFET" and "pFET" and (gate near4 electrode) and (bond\$4 near4 (semiconductor or wafer or substrate)) and (open\$4 or via or trench or hole) and stress	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 11:57
S5	9	(semiconductor or wafer or substrate) and (active near4 region) and "nFET" and "pFET" and (gate near4 electrode) and (bond\$4 near4 (semiconductor or wafer or substrate)) and (open\$4 or via or trench or hole) and stress and direction	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:47
S6	6	(semiconductor or wafer or substrate) and (active near4 region) and "nFET" and "pFET" and (gate near4 electrode) and (bond\$4 near4 (semiconductor or wafer or substrate)) and (implant\$4 near4 oxygen)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:48

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S7	6	(semiconductor or wafer or substrate) and (active near4 region) and "nFET" and "pFET" and (gate near4 electrode) and (bond\$4 near4 (semiconductor or wafer or substrate)) and (implant\$4 near4 oxygen) and (anneal or thermal or heat)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:48
S8	86899	(surface near region)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/15 17:00
S9	266	(surface near region) and ("pfet" or (p near fet)) and ("nfet" or (n near fet))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/15 17:01
S10	265	(surface near region) and ("pfet" or (p near fet)) and ("nfet" or (n near fet)) and (wafer or substrate or carrier or base)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/15 17:02
S11	60	(surface near region) and ("pfet" or (p near fet)) and ("nfet" or (n near fet)) and (wafer or substrate or carrier or base) and ((different or opposite) near9 surface)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/15 17:03
S12	39	(surface near region) and ("pfet" or (p near fet)) and ("nfet" or (n near fet)) and (wafer or substrate or carrier or base) and (different near9 surface)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/15 17:04
S13	19	(surface near region) and ("pfet" or (p near fet)) and ("nfet" or (n near fet)) and (wafer or substrate or carrier or base) and (different near surface)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/15 17:04

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S14	5	(surface near region) and ("pfet" or (p near fet)) and ("nfet" or (n near fet)) and (wafer or substrate or carrier or base) and ((different near surface) near region)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/15 17:04
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